

FIG. 1

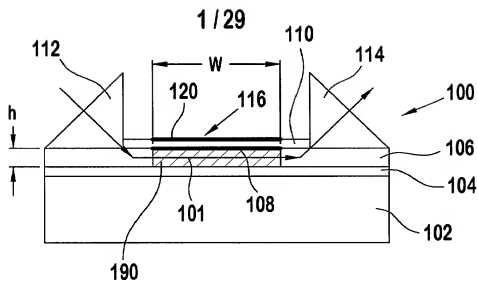


FIG. 2

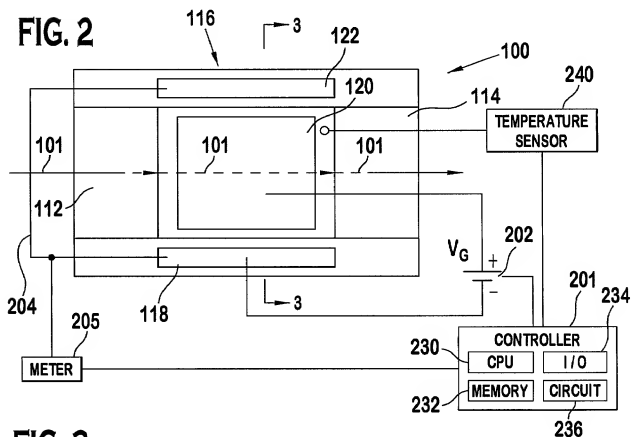


FIG. 3

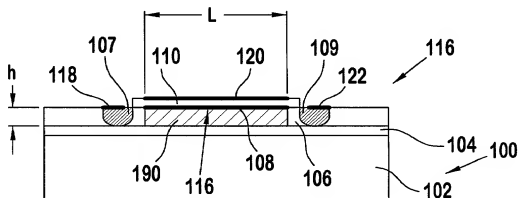


FIG. 4

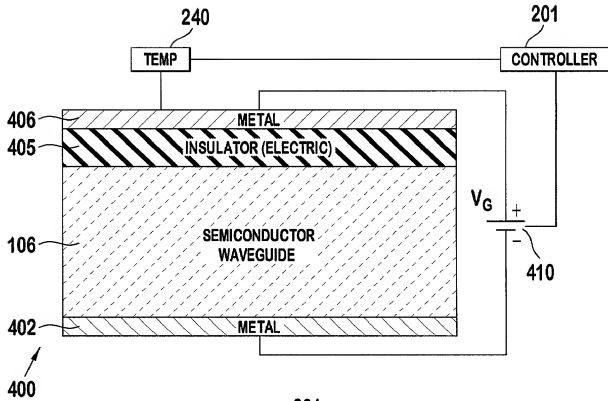


FIG. 5

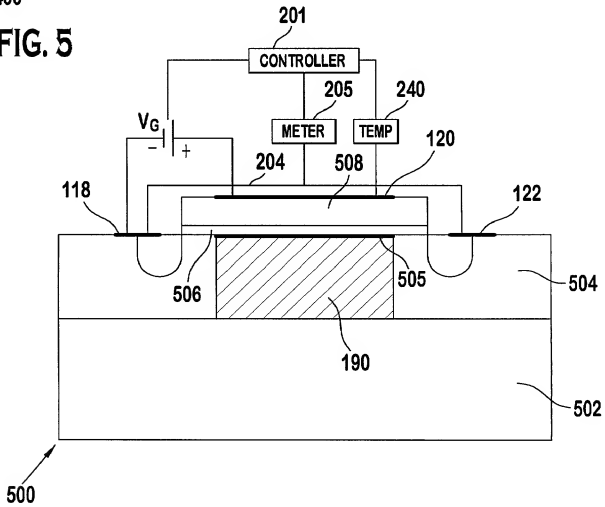


FIG. 6

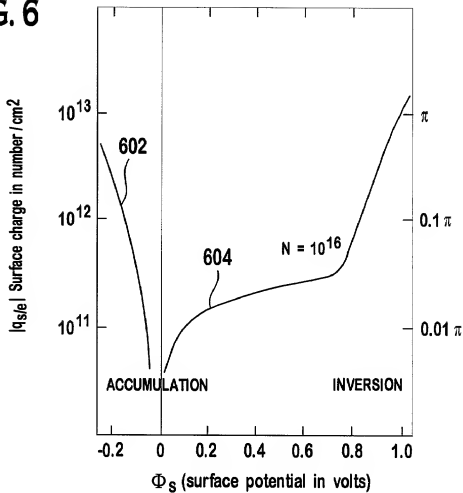
Phase shift for 3 mm long device with 0.2 μm waveguide

FIG. 7

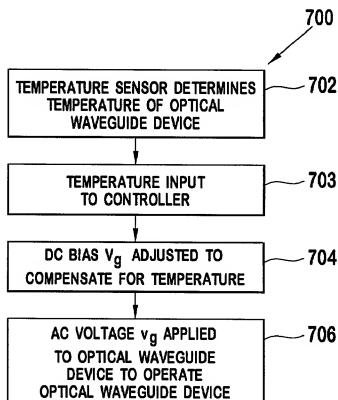


FIG. 9

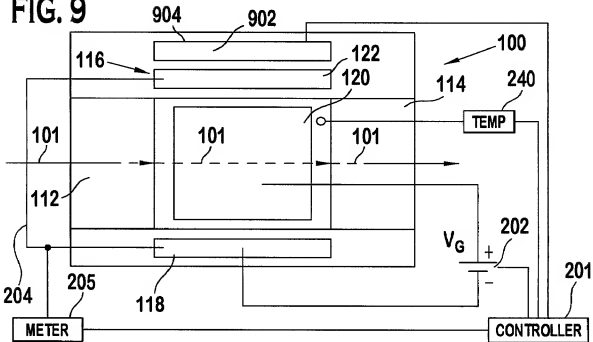


FIG. 10

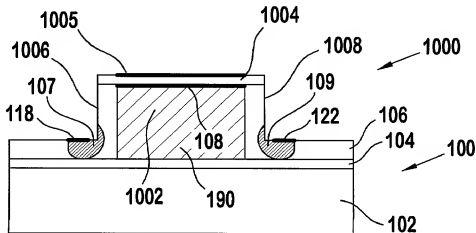


FIG. 11

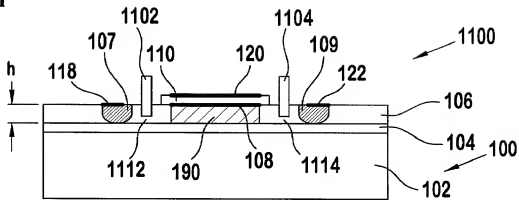


FIG. 12

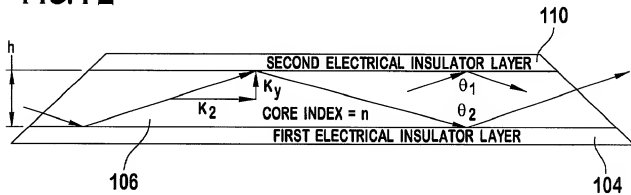
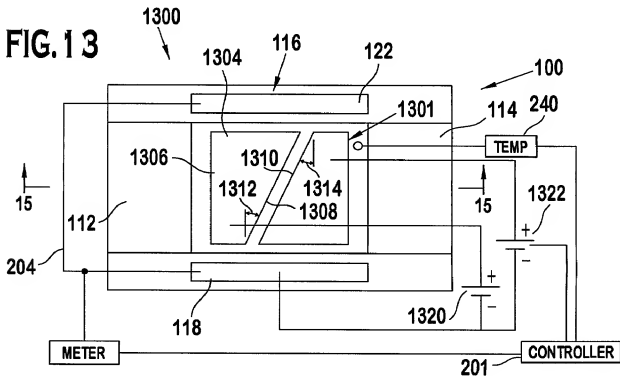


FIG. 13



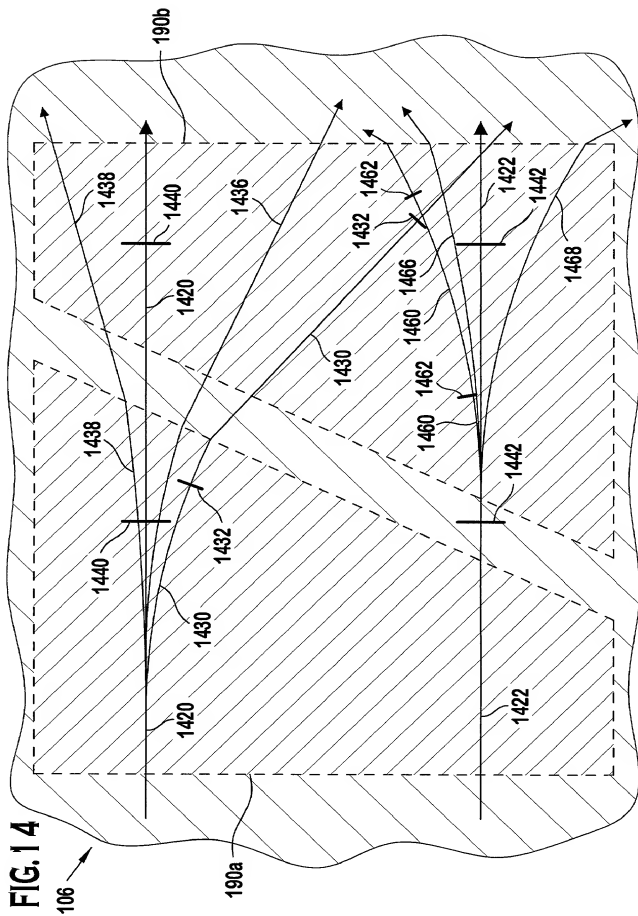


FIG. 15A

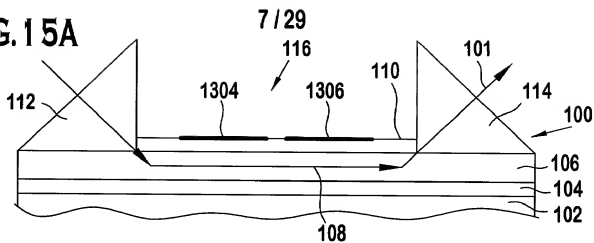


FIG. 15B

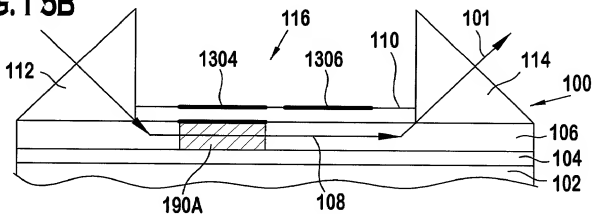


FIG. 15C

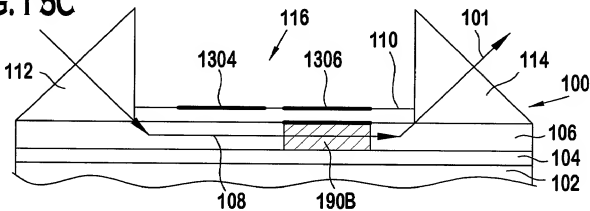


FIG. 15D

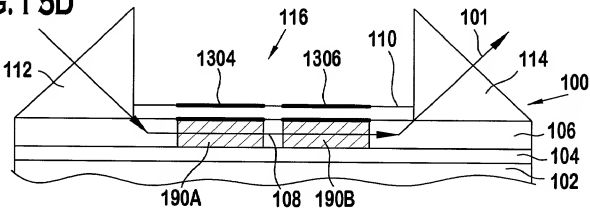


FIG. 16

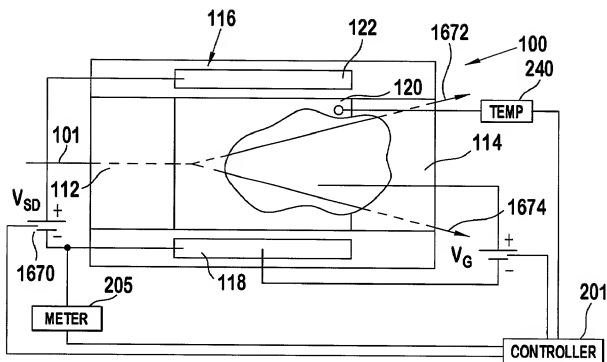


FIG. 17

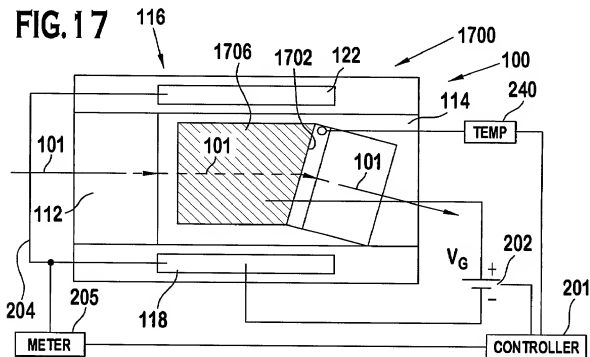


FIG. 18

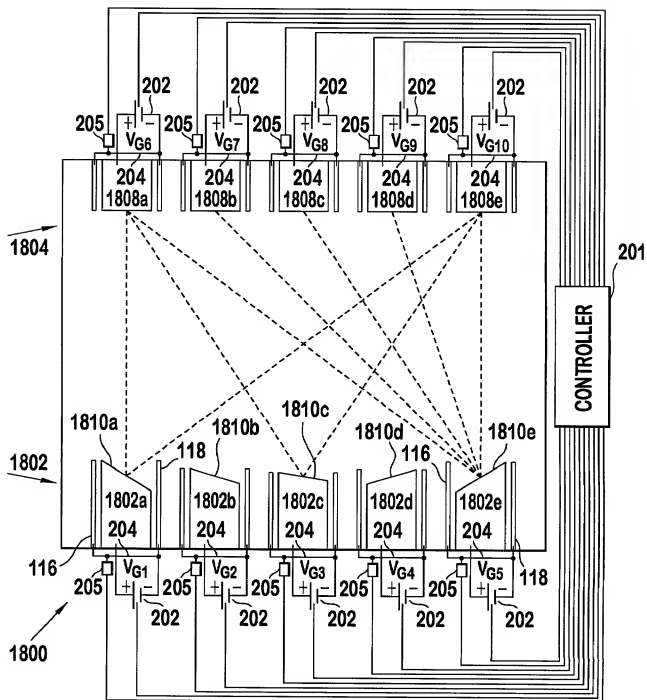


FIG. 19

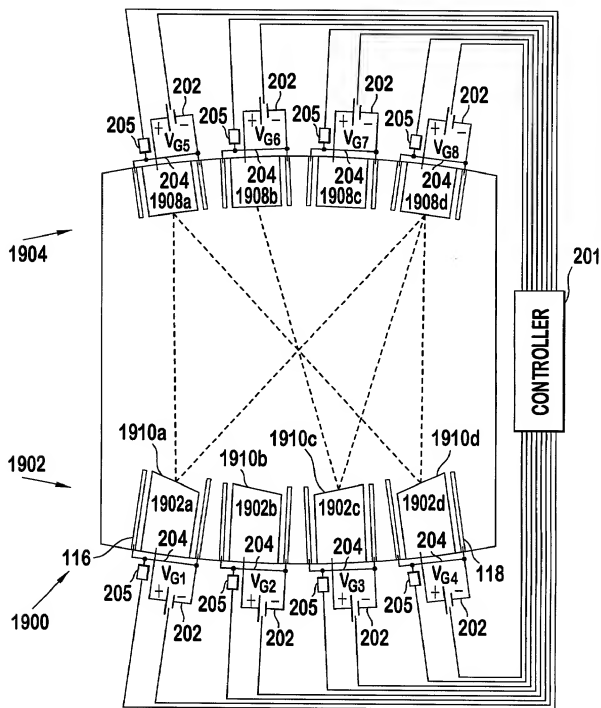


FIG. 20

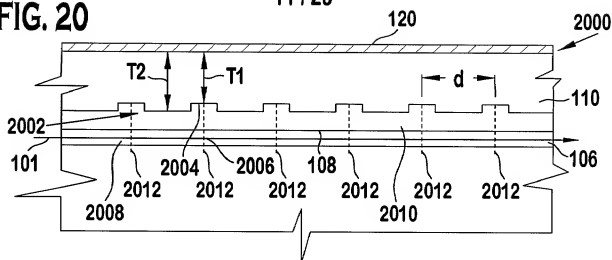


FIG. 21

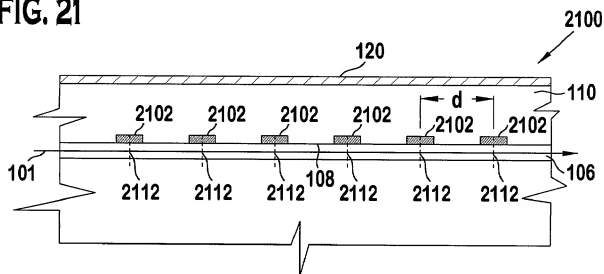


FIG. 22

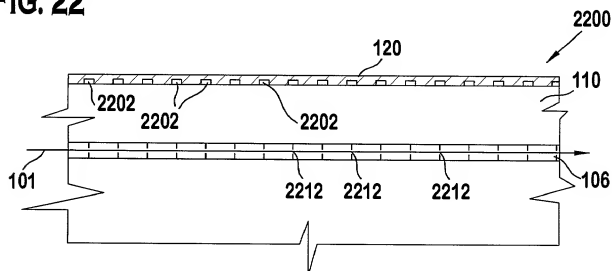


FIG. 23

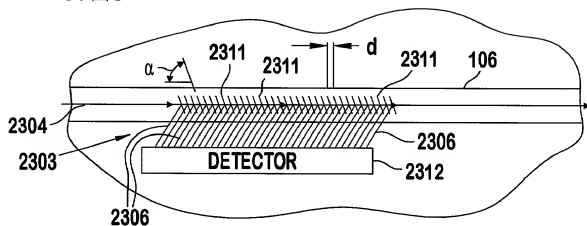


FIG. 24

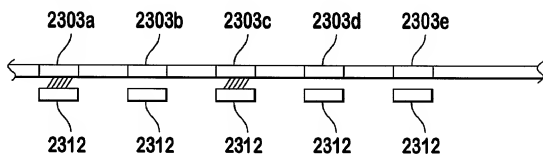


FIG. 25

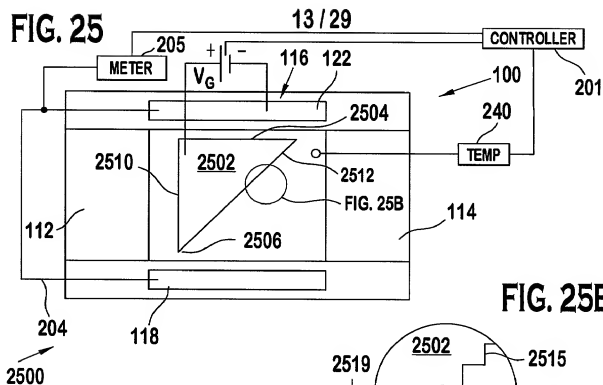


FIG. 25B

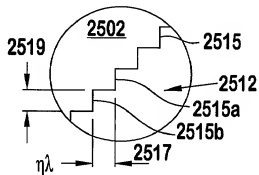


FIG. 26

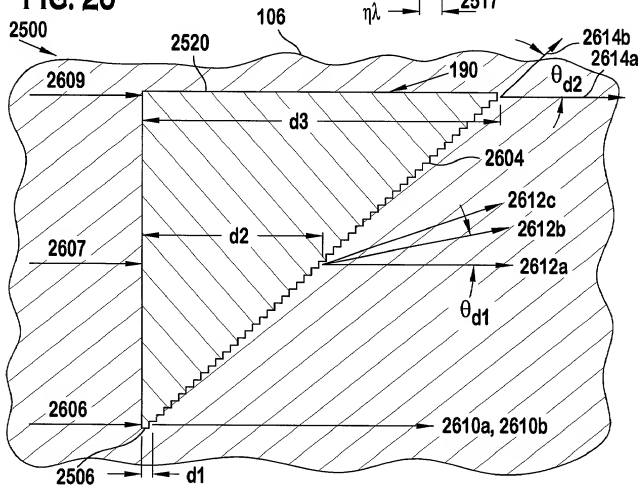


FIG. 10 is a schematic diagram of a semiconductor device 100. The device includes a substrate 101 with a central region 120 containing a stack of layers 120a and 120b. A gate voltage V_G is applied to the central region 120. The device is connected to a meter 205 and a controller 201. A temperature sensor 240 is also shown.

FIG. 31

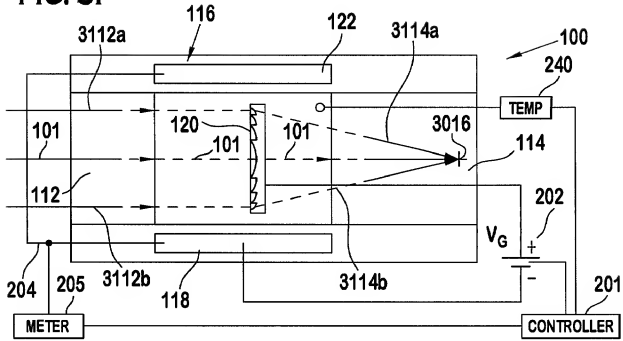


FIG. 31 A

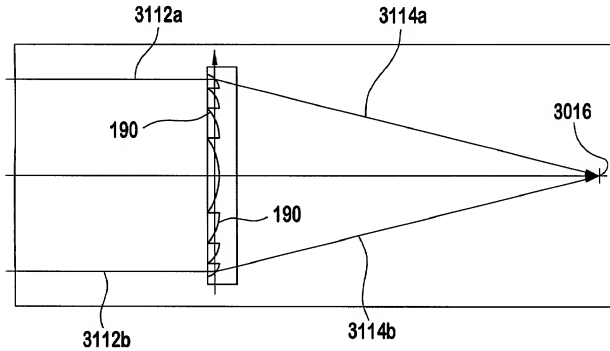


FIG. 33

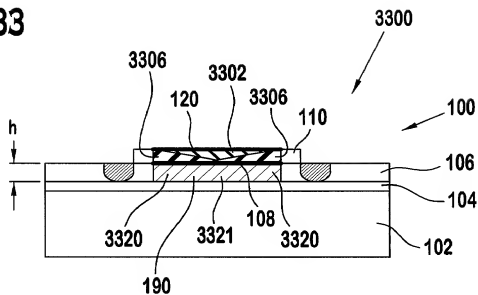


FIG. 34

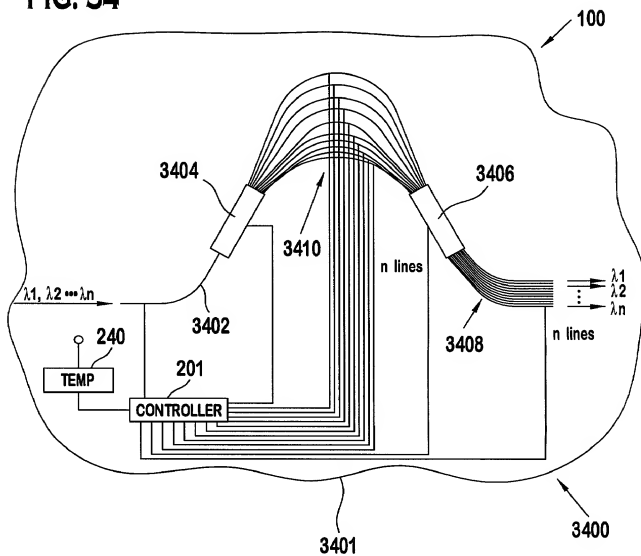


FIG. 35

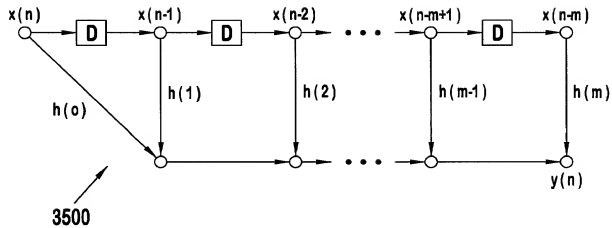


FIG. 36

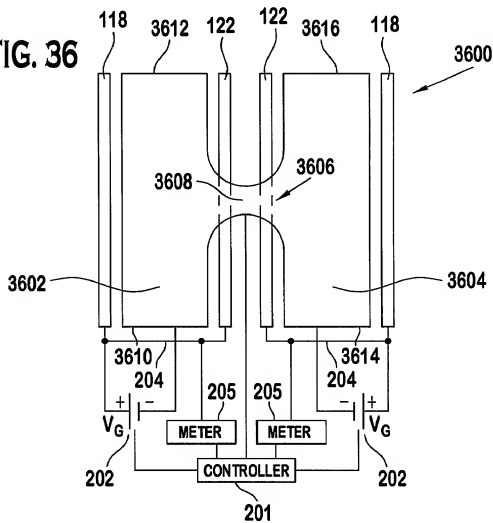


FIG. 37

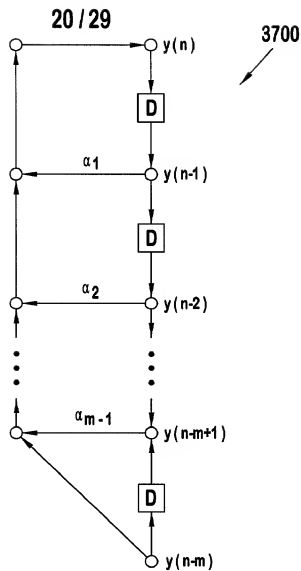


FIG. 38

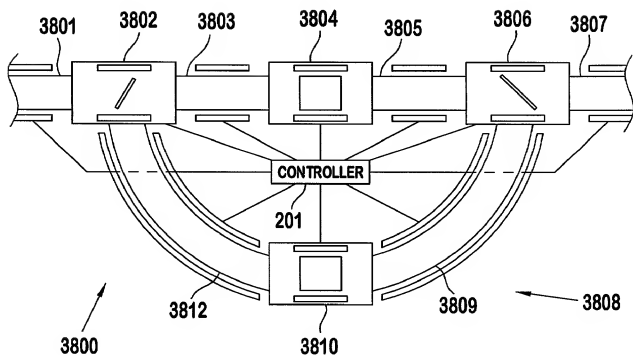


FIG. 39

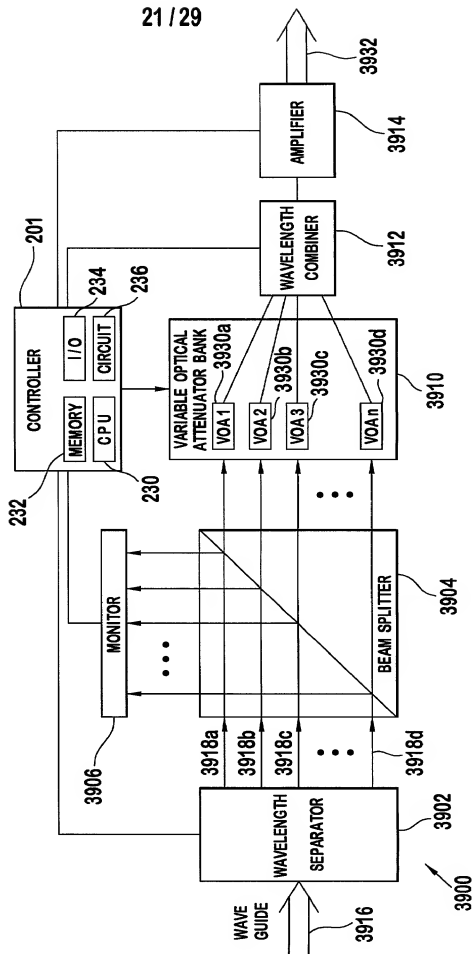


FIG. 40

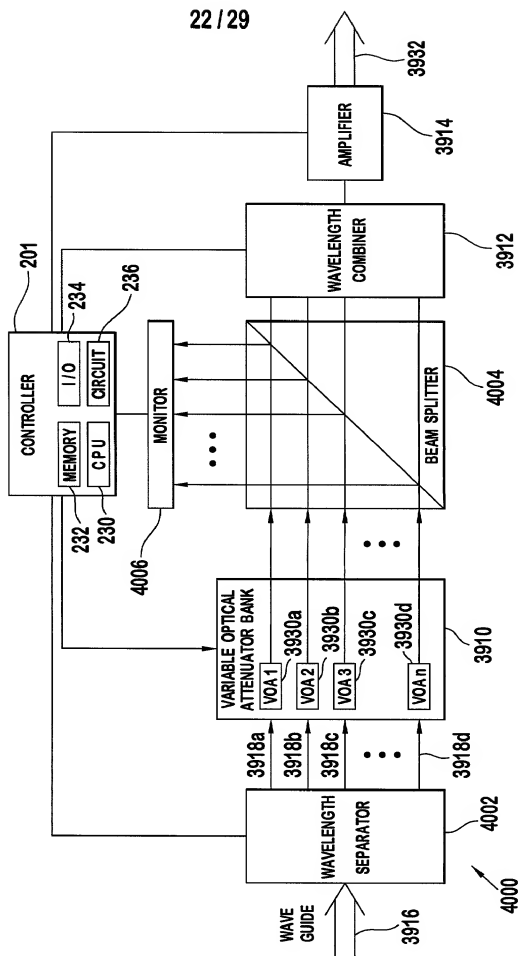


FIG. 4I

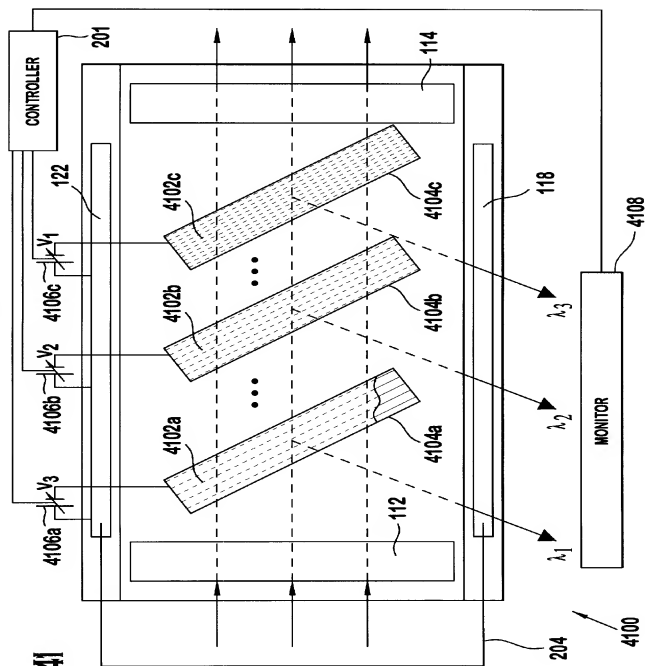


FIG. 42

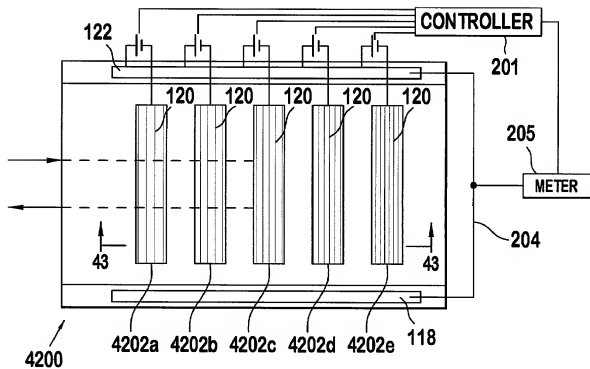
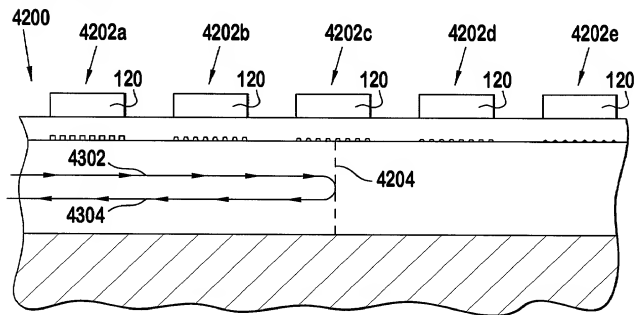


FIG. 43



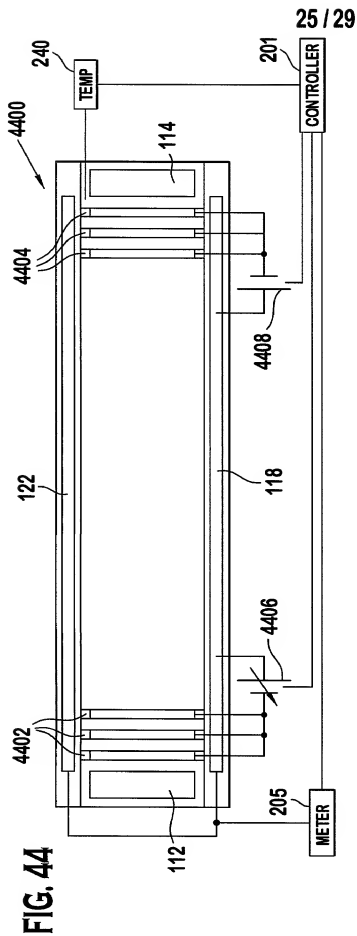


FIG. 45

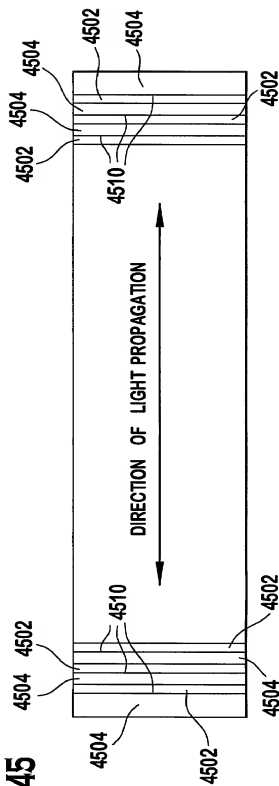


FIG. 46

TO COUPLER OR OTHER DEVICE 100

4610

116

4602

122

120

4600

114

101

112

4604

4612

TO COUPLER OR OTHER DEVICE 100

240

TEMP

202

V_G

204

205

118

4606

4614

METER

CONTROLLER

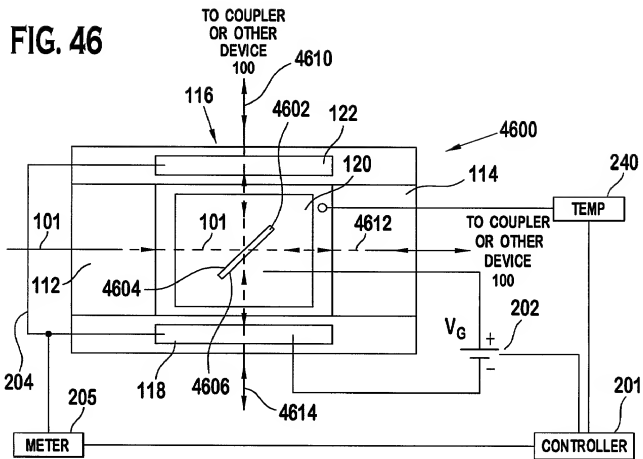


FIG. 47

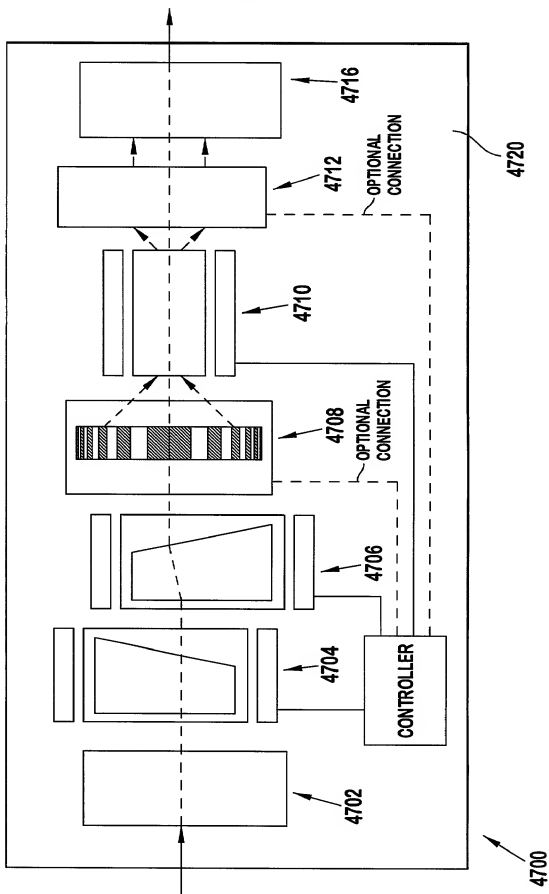


FIG. 48

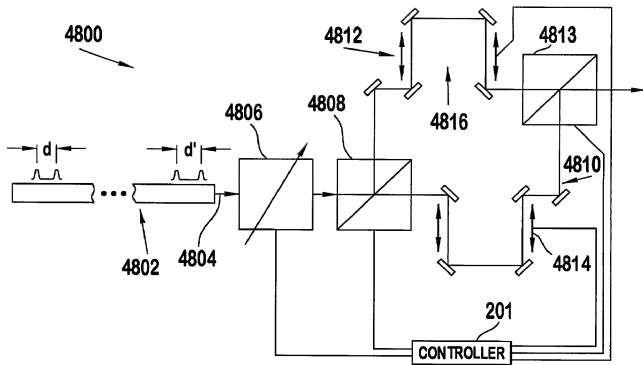


FIG. 49

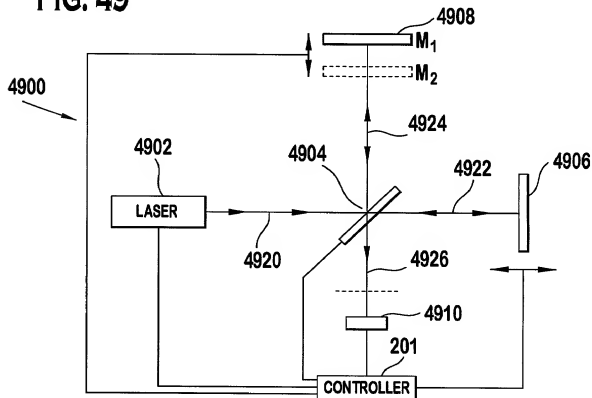


FIG. 50

